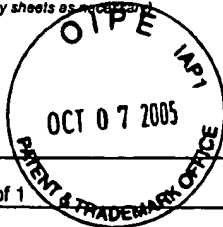


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Application Number	10/783,695
Filing Date	February 20, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	2891
Examiner Name	Smith, Bradley

Sheet 1 of 1

Attorney Docket No: 1303.019US2

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 6

Attorney Docket No: 1303.019US2

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Examin or Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 6

Attorney Docket No: 1303.019US2

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 3 of 6

Attorney Docket No: 1303.019US2

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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EXAMINER

DATE CONSIDERED

12/12/02

Substitute Disclosure Statement Form (PTO-1449)

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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 4 of 6		Attorney Docket No: 1303.019US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-Issue number(s), publisher, city and/or country where published.	T ²
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EXAMINER

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Substitute Disclosure Statement Form (PTO-1449)
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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Attorney Docket No: 1303.019US2

Sheet 5 of 6

OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

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